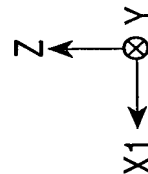


This cross-sectional diagram illustrates a semiconductor device with several distinct layers and regions. The top surface is labeled 167, followed by layer 166. Below these are layers 8 and 6. A central region is divided into three vertical sections labeled 7a, 7c, and 7b, which are collectively grouped under label 7. Arrows indicate current flow or carrier movement within these sections. Other labels include 5, 4, 3, 2, 164, 163, and 200, representing different material layers or interfaces. On the left side, dimensions G_2 and TW are indicated. At the bottom, forces F_1 and F_2 are shown acting on the base layer 1. The entire structure is identified as K, 151.



2 / 10

FIG. 2

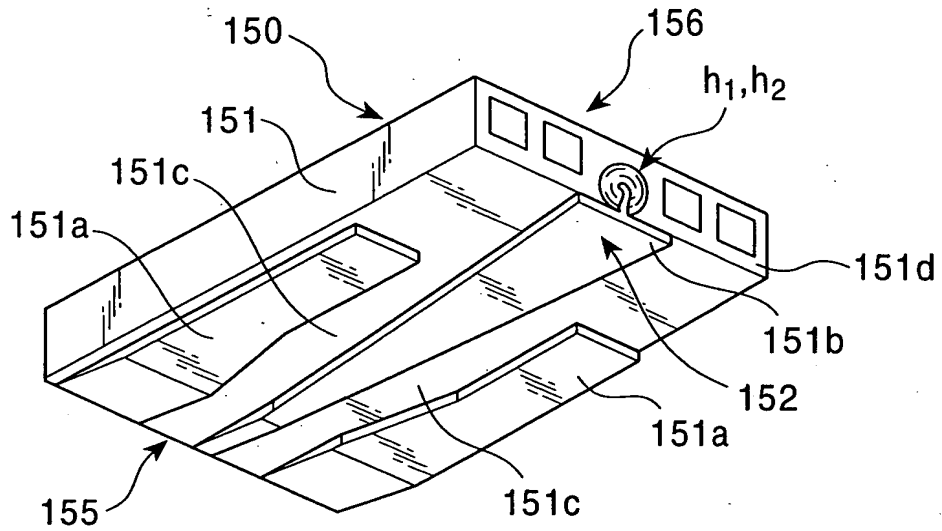


FIG. 3

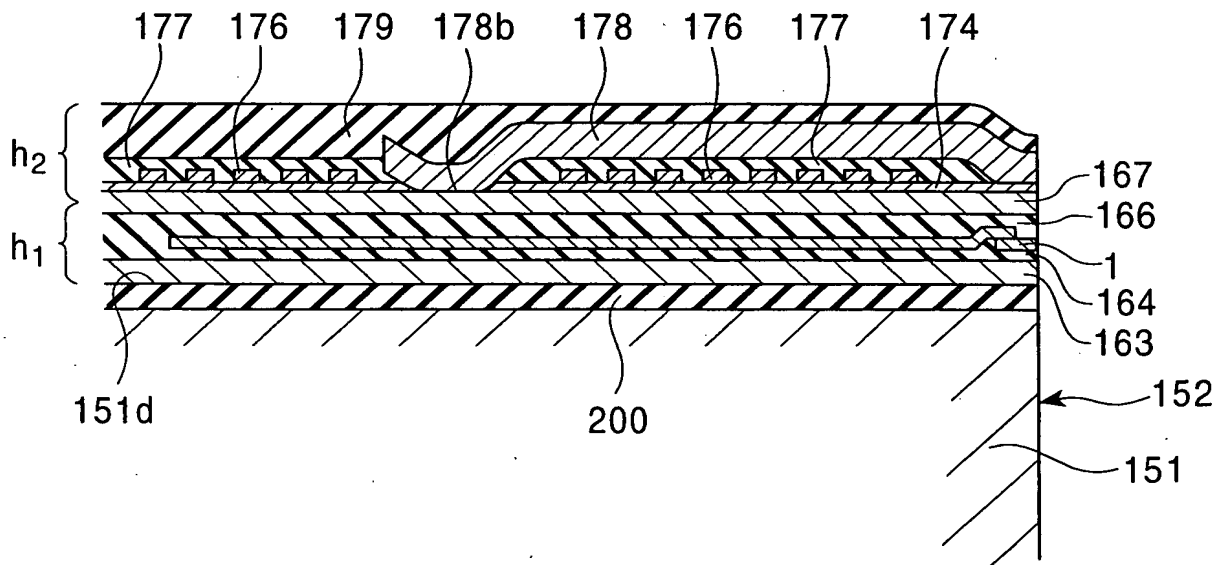


FIG. 4

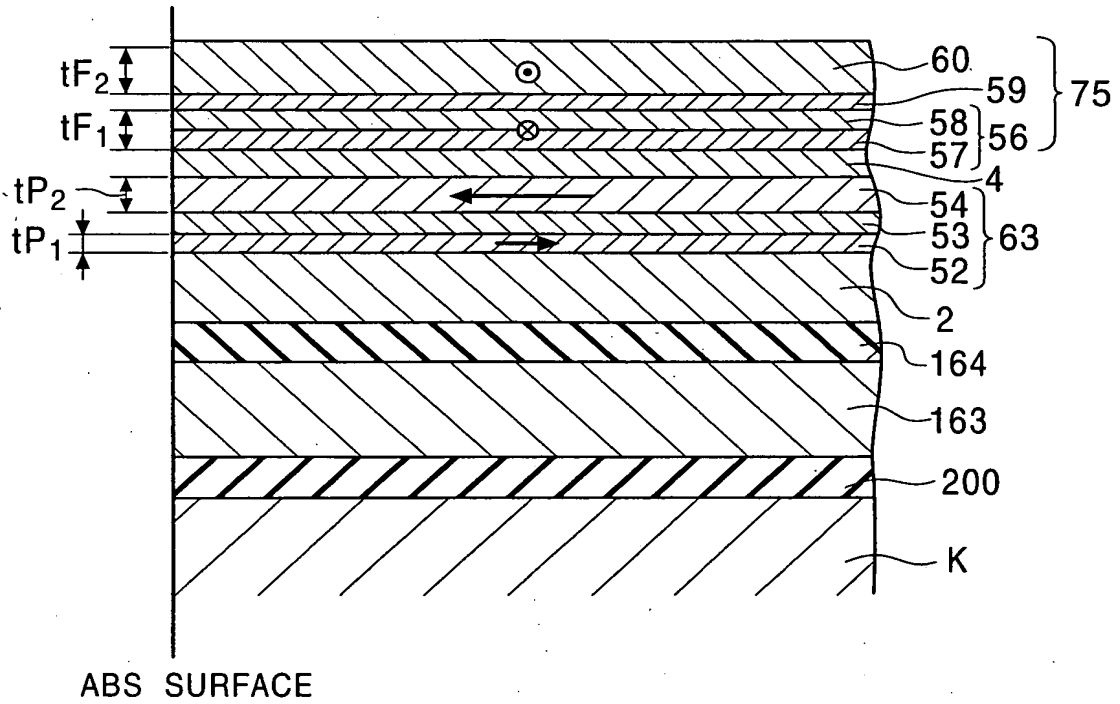


FIG. 5

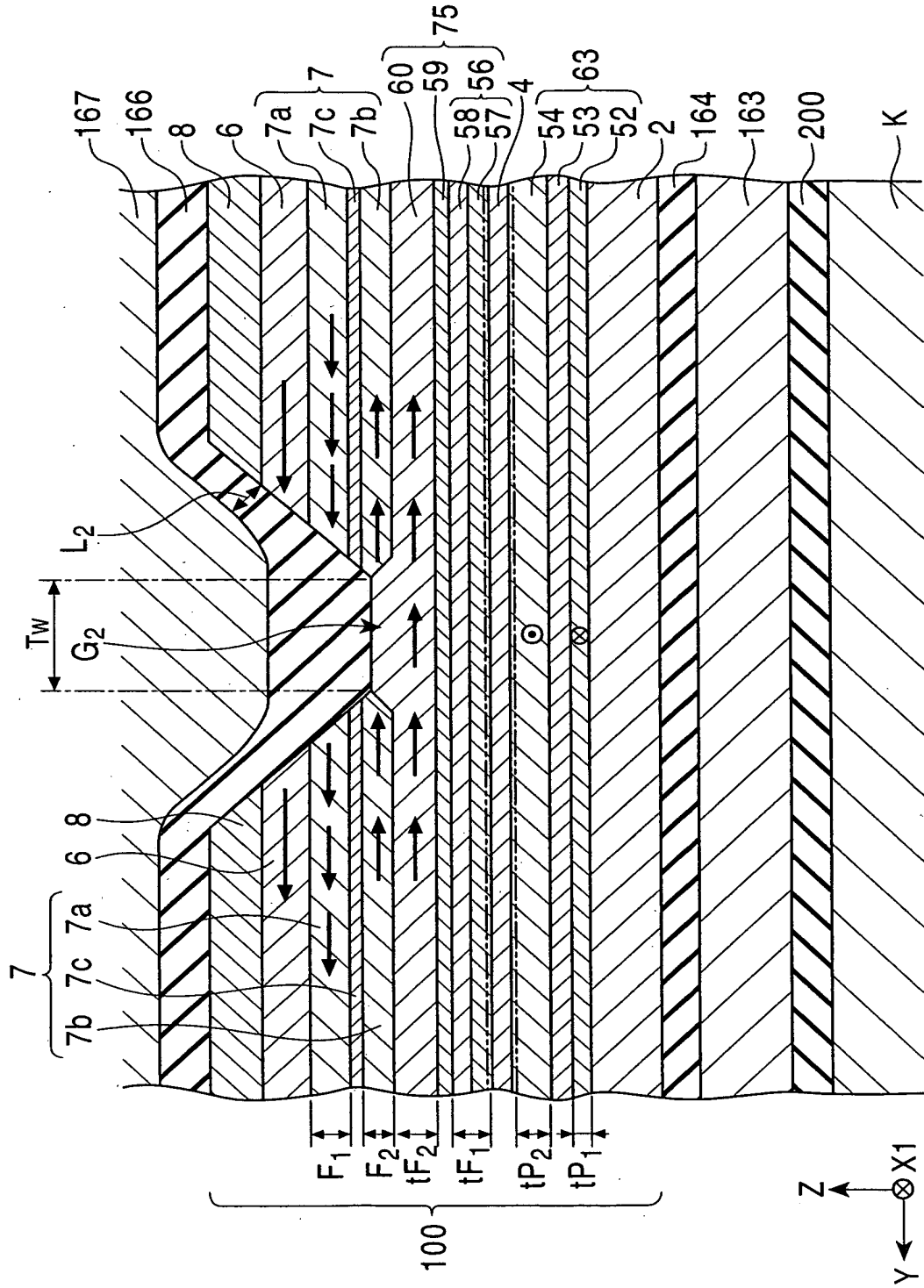
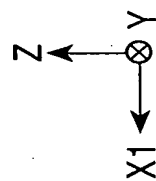
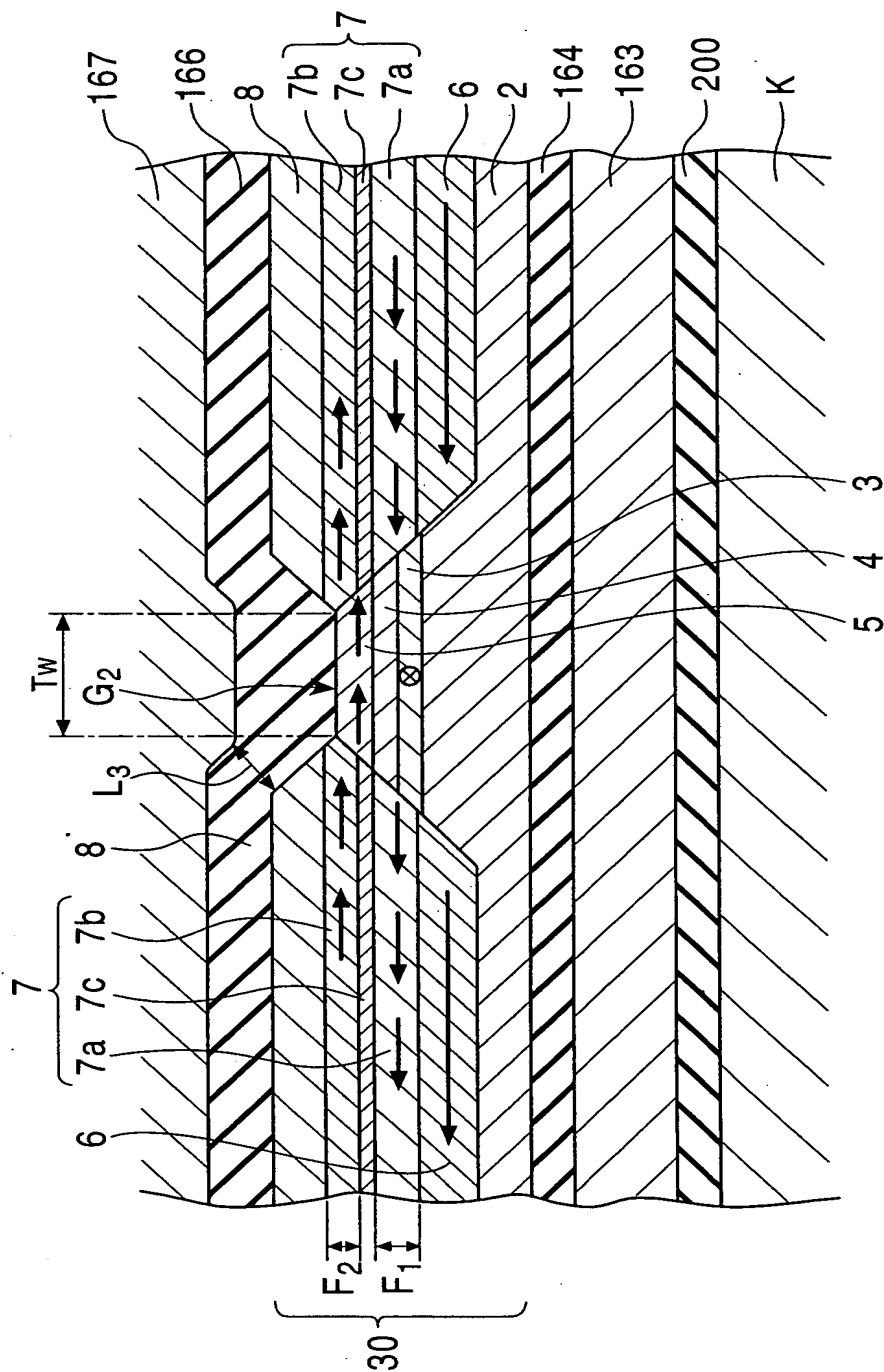


FIG. 6



6 / 10

FIG. 7

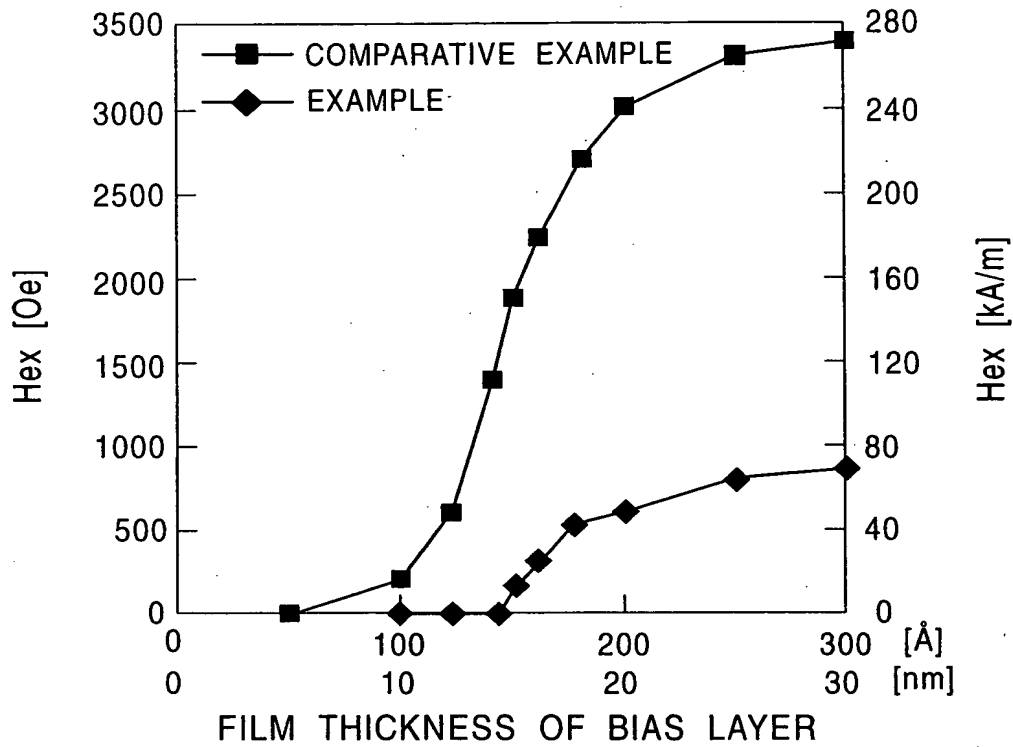


FIG. 8

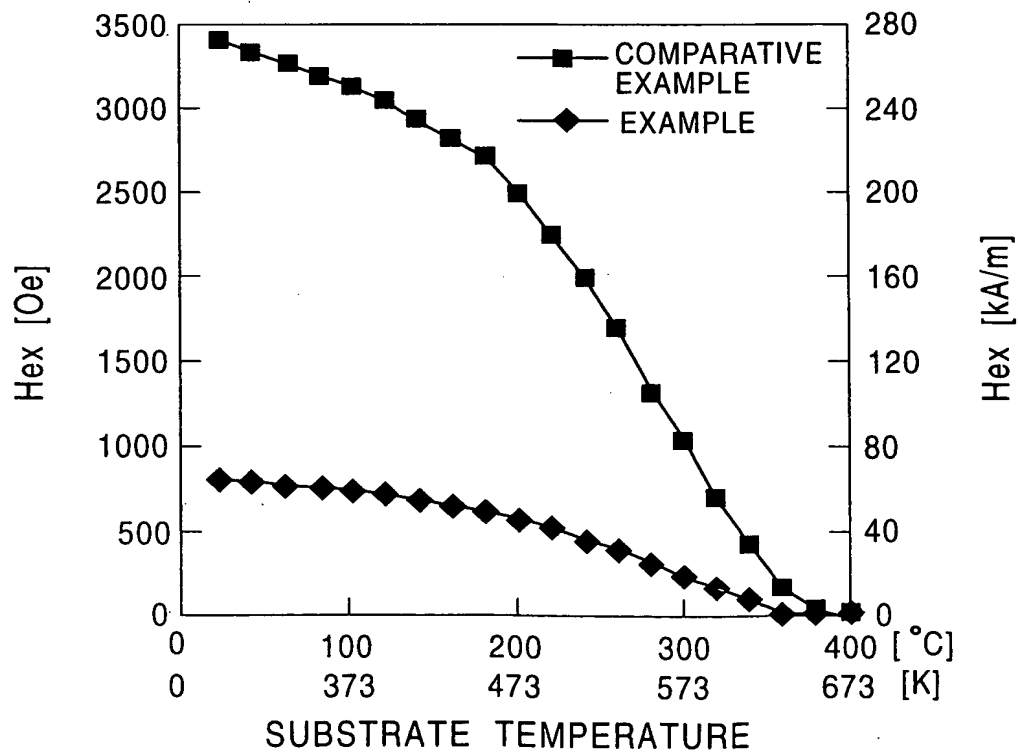


FIG. 9
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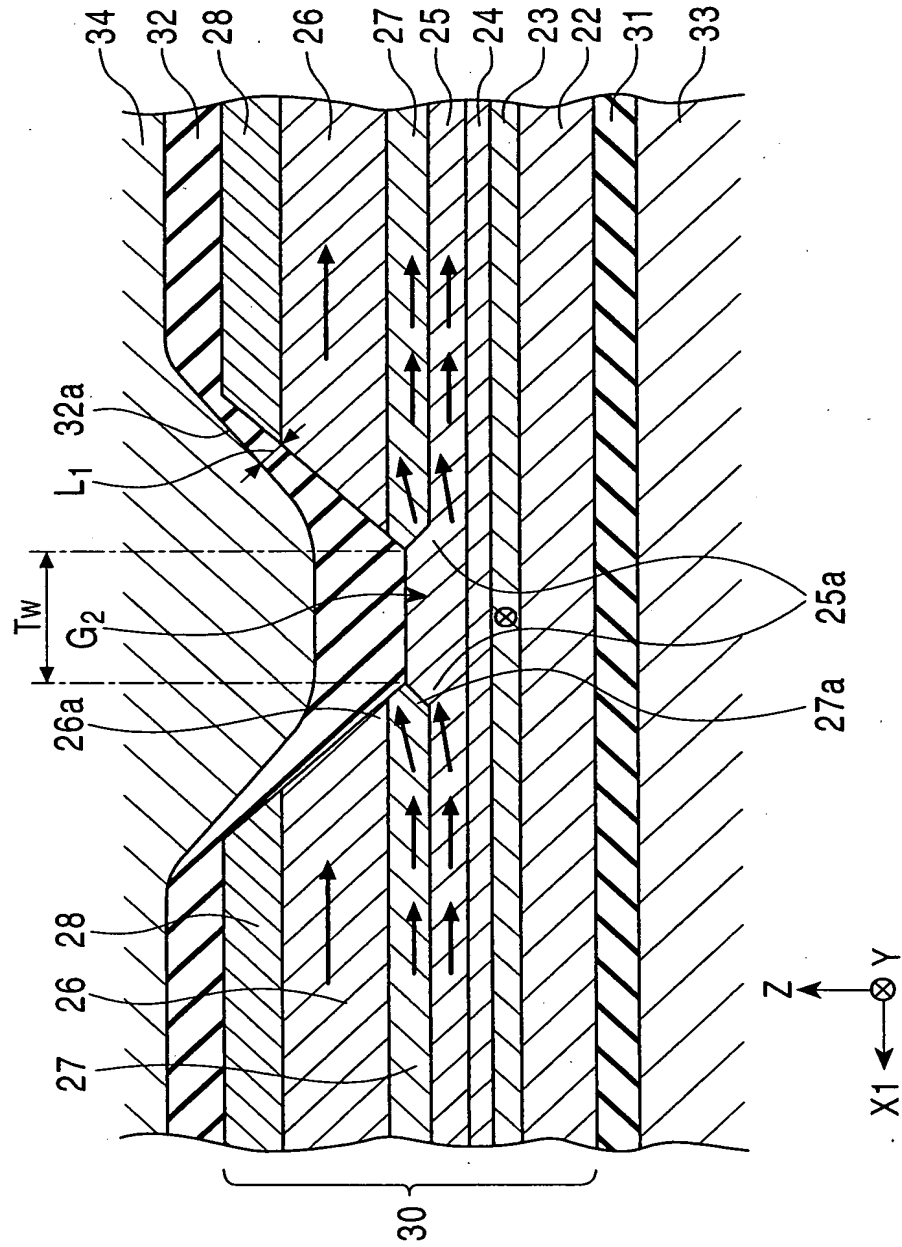


FIG. 10

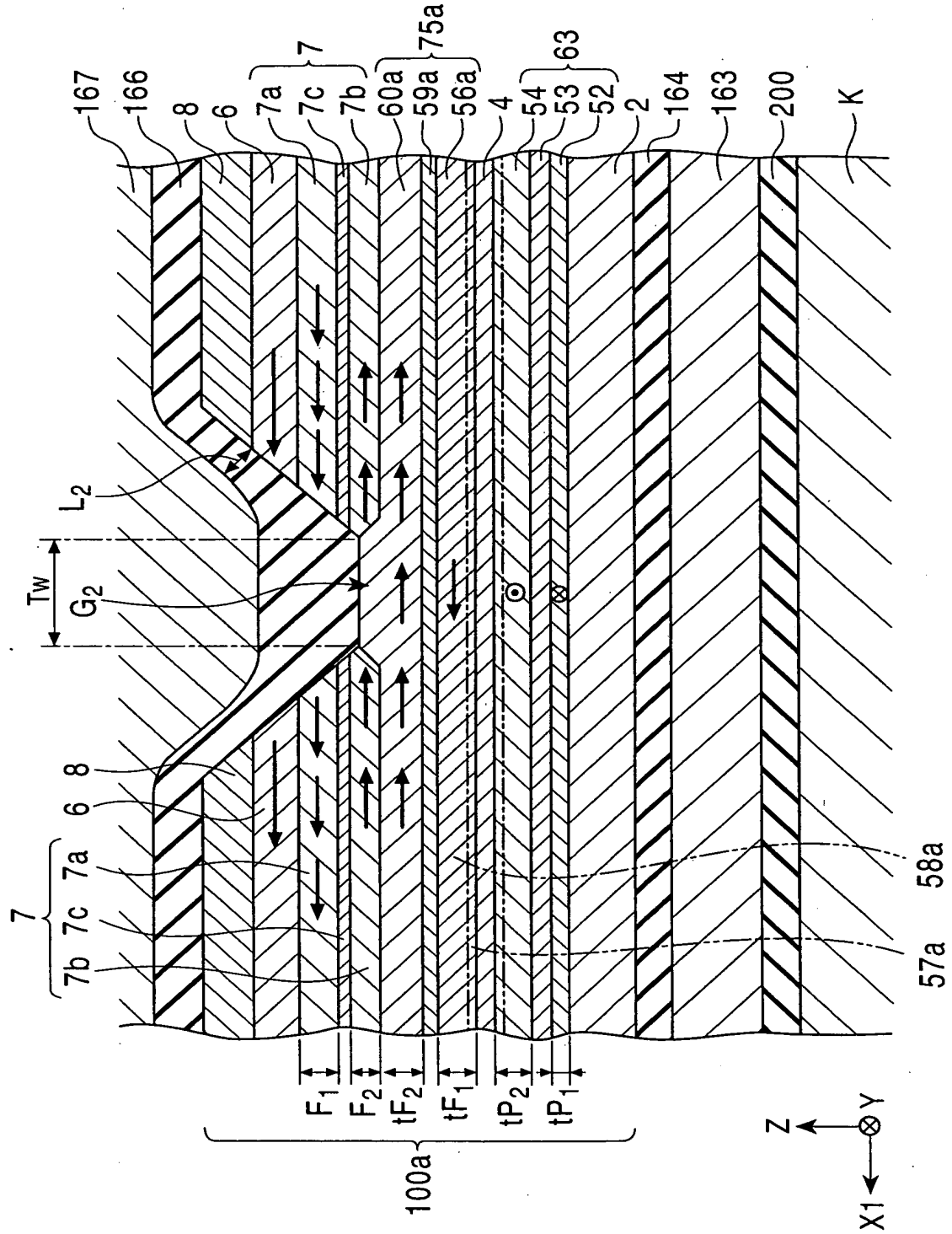


FIG. 11

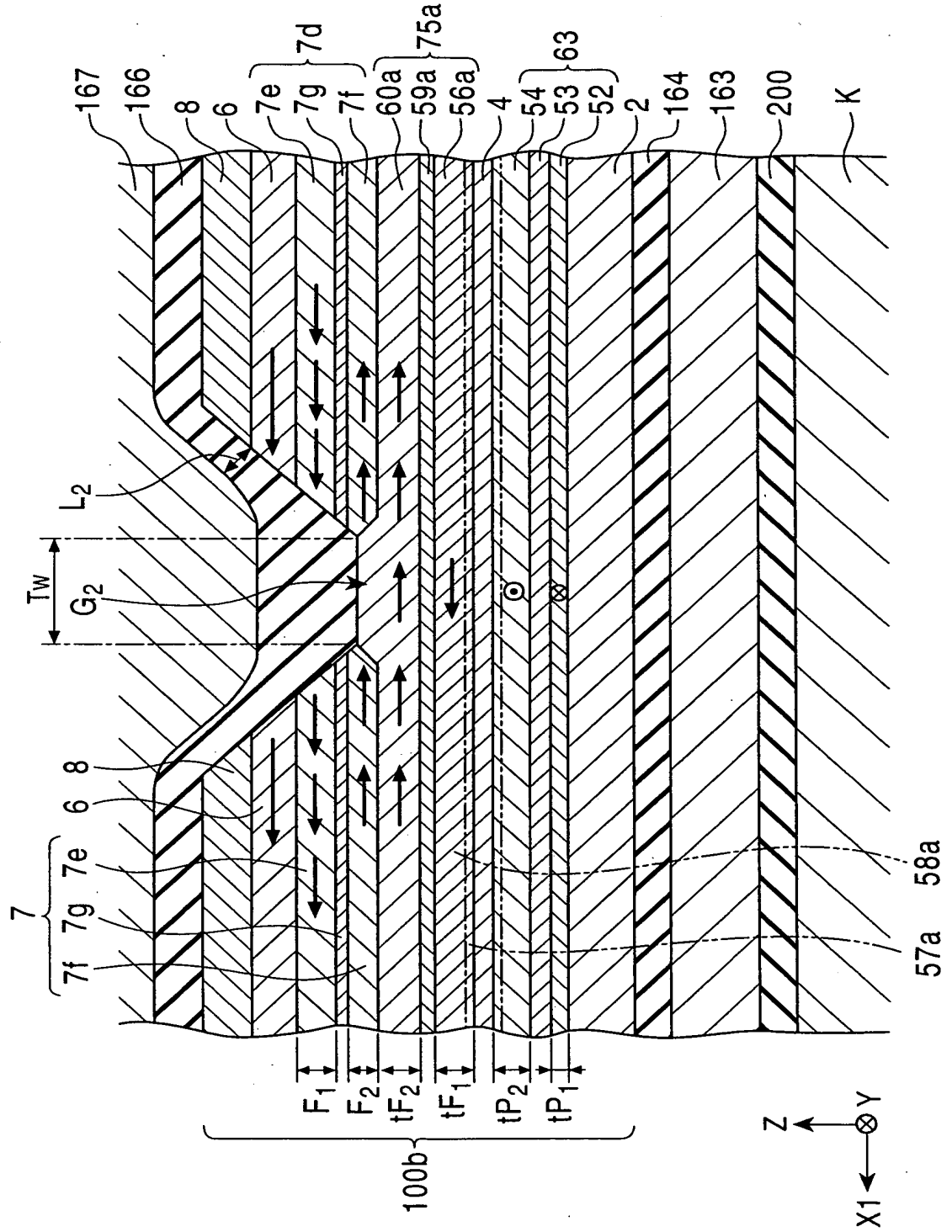


FIG. 12

